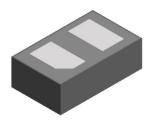


PESDHC2FD4V5BHM

Bi-directional 4.5V High Capacitance ESD Protector

Description

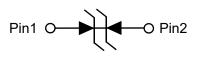
The PESDHC2FD4V5BHM protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, low operating voltage. It gives designer the flexibility to protect one bi-directional line in applications where arrays are not practical.



DFN1006-2L(Bottom View)

Feature

- > 500W peak pulse power per line ($t_P = 8/20\mu s$)
- DFN1006-2L package
- Response time is typically < 1 ns</p>
- Bidirectional configurations
- Low clamping voltage
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD) ±30kV(air), ± 30kV(contact); IEC 61000-4-5 (Lightning) 45A (8/20us)



Circuit Diagram



Applications

- > Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
- Peripherals

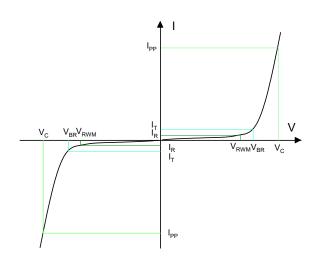
Mechanical Characteristics

- > Mounting position: Any
- Qualified max reflow temperature:260°C
- Device meets MSL 1 requirements
- DFN1006-2L without plating

PESDHC2FD4V5BHM

Electronics Parameter

Symbol	Parameter		
V _{RWM}	Peak Reverse Working Voltage		
I _R	Reverse Leakage Current @ V_{RWM}		
V _{BR}	Breakdown Voltage @ I _T		
Ι _Τ	Test Current		
I _{PP}	Maximum Reverse Peak Pulse Current		
V _c	Clamping Voltage @ I _{PP}		
P _{PP}	Peak Pulse Power		
CJ	Junction Capacitance		
I _F	Forward Current		
V _F	V _F Forward Voltage @ I _F		



Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V _{RWM}	-	-	-	4.5	V
Breakdown Voltage	V _{BR}	I _t = 1mA	4.7	-	6.0	V
Reverse Leakage Current	I _R	V _{RWM} = 4.5V	-	-	1	μA
Clamping Voltage ¹⁾	V _c	TLP = 16A, t _p = 100ns	-	6.5	-	V
Dynamic resistance ¹⁾	R _{DYN}	-	-	0.03	-	Ω
Clamping Voltage ²⁾	V _c	I _{PP} = 30A,t _P = 8/20μs	-	8.5	10	V
		I _{PP} = 45A,t _P = 8/20μs	-	10.5	12	V
Junction Capacitance	C」	V _R = 0V,f = 1MHz	-	100	150	pF

Notes:

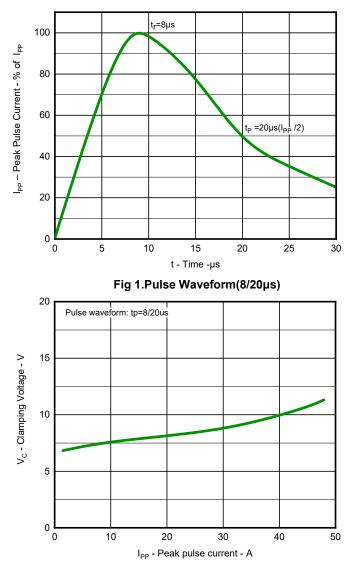
1.TLP parameter: $Z_0=50\Omega$, $t_p=100$ ns, $t_r=2$ ns, averaging window from 60 ns to 80 ns. R_{DYN} is calculated from 4A to 16A. 2.Non-repetitive current pulse, according to IEC61000-4-5.

Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Peak Pulse Power(t _P = 8/20µs)	P _{PP}	500	W
Peak Pulse Current (t _P = 8/20µs)	I _{PP}	45	А
Lead Soldering Temperature	Τ _L	260 (10 sec)	°C
Junction and Storage Temperature Range	T _{J,} T _{STG}	-55~+150	°C
ESD Protection-Contact Discharge	V _{ESD}	±30	kV
ESD Protection-Air Discharge	V _{ESD}	±30	kV

PESDHC2FD4V5BHM

Typical Characteristics





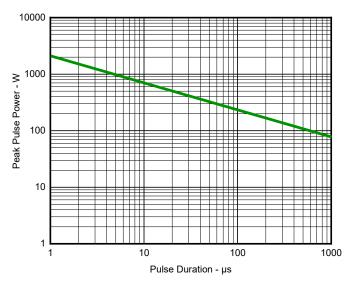
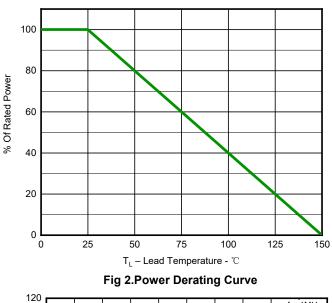
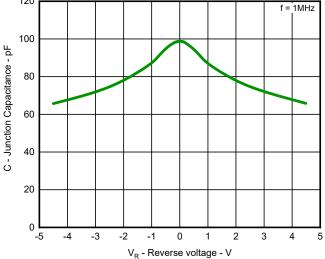
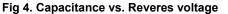
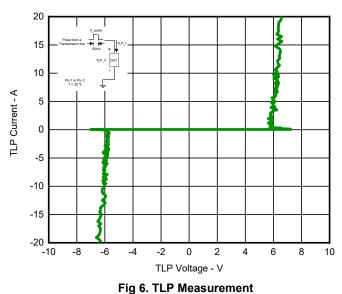


Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time

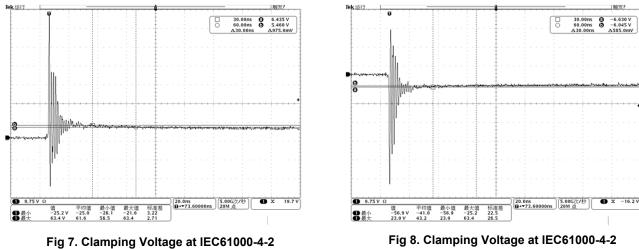




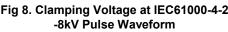




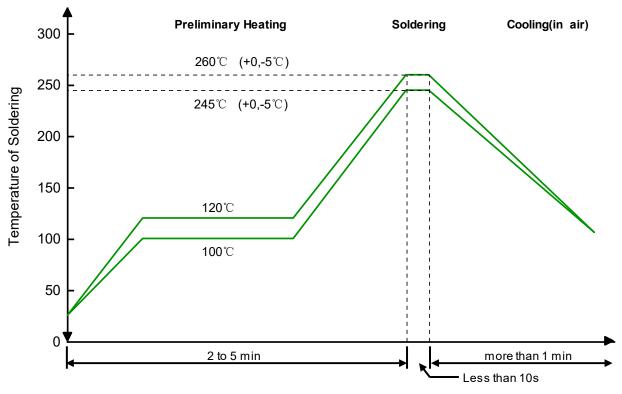
PESDHC2FD4V5BHM



+8kV Pulse Waveform



Solder Reflow Recommendation



Remark: Pb free for 260°C; Pb for 245°C.

PESDHC2FD4V5BHM

ESD Protector

PCB Design

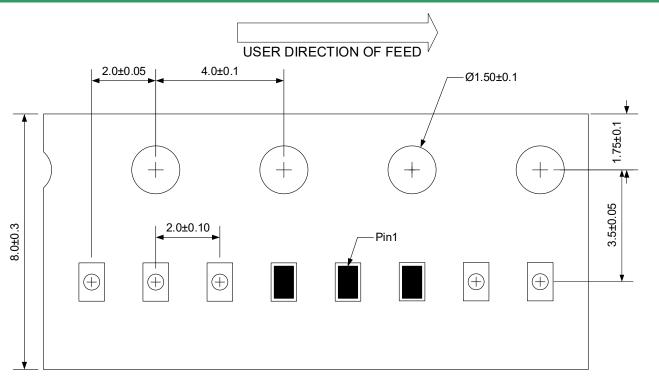
For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- > Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- > Do not make false economies and save copper for the ground connection.
- > Place via holes to ground as close as possible to the anode of the TVS diode.
- ➢ Use as many via holes as possible for the ground connection.
- > Keep the length of via holes in mind! The longer the more inductance they will have.

Ordering information

Device	Package	Reel	Shipping	
PESDHC2FD4V5BHM	DFN1006-2L (Pb-Free)	7"	10000 / Tape & Reel	

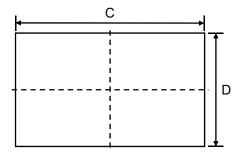
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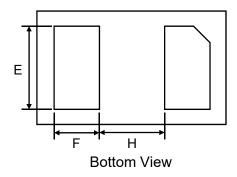
Unit:mm

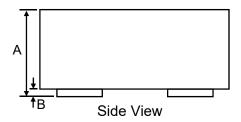
PESDHC2FD4V5BHM

Product dimension (DFN1006-2L)

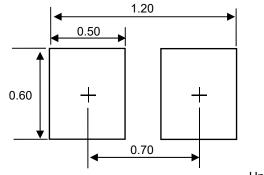








Dim	Millim	neters	Inches		
Dim	Min	Max	Min	Max	
А	0.340	0.498	0.013	0.020	
В	0.000	0.050	0.000	0.002	
С	0.950	1.080	0.037	0.043	
D	0.550	0.680	0.022	0.027	
E	0.400	0.600	0.016	0.024	
F	0.200	0.300	0.008	0.012	
н	0.400 Typ.		0.015 Typ.		



Unit:mm



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